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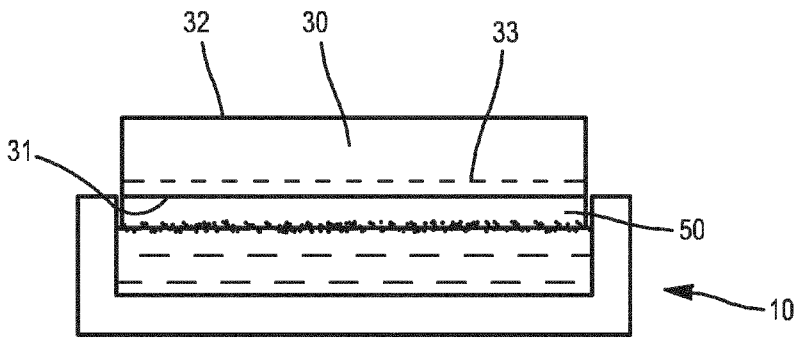
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(54) **Title**: METHOD AND DEVICE FOR FABRICATING A LAYER IN SEMICONDUCTOR MATERIAL

FIG. 3



(57) **Abstract**: The invention concerns a method for fabricating a substrate in semiconductor material characterized in that it comprises the steps of: Starting from a donor substrate (30) in a first semiconductor material at an initial temperature, Contacting a surface (31) of the donor substrate (30) with a bath (20) of a second semiconductor material held in the liquid state at a temperature higher than said initial temperature, the second semiconductor material being chosen so that its melting point is equal to or lower than the melting point of the first semiconductor material, Solidifying the bath material on said surface (31) to thicken the donor substrate (30) with a solidified layer. The invention also concerns a device for implementing said method.